

Thyristor Module

MCMA650MT1800NKD

advanced

1800 V

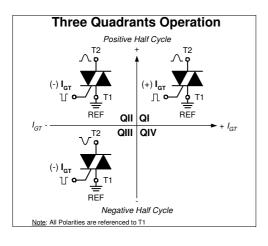
300 A

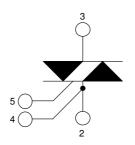
1,12 V

1~ Triac

Part number

MCMA650MT1800NKD







Backside: isolated

F1 E72873

Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation
- QI QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you. Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments; the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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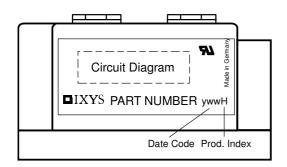
Rectifier				l	Ratings	l	! -
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forward	blocking voltage	$T_{VJ} = 25^{\circ}C$			1900	٧
V _{RRM/DRM}	max. repetitive reverse/forward bloc		$T_{VJ} = 25^{\circ}C$			1800	٧
I _{R/D}	reverse current, drain current	$V_{R/D} = 1800 \text{ V}$	$T_{VJ} = 25^{\circ}C$			1	m <i>P</i>
		$V_{R/D} = 1800 \text{ V}$	$T_{VJ} = 125^{\circ}C$			20	m <i>A</i>
V_{T}	forward voltage drop	$I_T = 300 A$	$T_{VJ} = 25^{\circ}C$			1,17	٧
		$I_{T} = 600 \text{ A}$				1,41	٧
		$I_T = 300 A$	$T_{VJ} = 125$ °C			1,12	٧
		$I_T = 600 \text{ A}$				1,42	٧
I _{TAV}	average forward current	$T_{\rm C} = 85^{\circ}{\rm C}$	$T_{VJ} = 140$ °C			300	Α
I _{RMS}	RMS forward current per phase	180° sine				650	P
V_{T0}	threshold voltage } for power loss	s calculation only	$T_{VJ} = 140$ °C			0,81	٧
r _T	slope resistance	o dalodiation only				1,01	mΩ
R _{thJC}	thermal resistance junction to case					0,12	K/W
R _{thCH}	thermal resistance case to heatsink				0,04		K/W
P_{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			960	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			9,50	k/
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			10,3	k/
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			8,08	k/
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			8,72	k/
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			451,3	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			437,9	kA2s
		t = 10 ms; (50 Hz), sine	T _{VJ} = 140°C			326,0	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			316,3	kA2s
C _J	junction capacitance	V _R = 400 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		438		рF
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_{\rm C} = 140^{\circ} \rm C$			120	W
	,	t _P = 300 μs				60	W
P_{GAV}	average gate power dissipation					20	W
(di/dt) _{cr}	critical rate of rise of current	T _{v.i} = 140°C; f = 50 Hz	epetitive, $I_{\tau} = 900 \text{ A}$			100	A/μs
701		$t_{P} = 200 \mu s; di_{G}/dt = 1 A/\mu s;$					<u>'</u>
		• •	ion-repet., $I_T = 300 \text{ A}$			500	A/μs
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	T _{VI} = 140°C			1000	i
(, and the second	R _{GK} = ∞; method 1 (linear volta	***				
V _{GT}	gate trigger voltage	V _D = 6 V	$T_{VJ} = 25^{\circ}C$			2	V
- 61			$T_{VJ} = -40$ °C			3	V
I _{GT}	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 25^{\circ}C$			300	m/
•GT	gate ingger carrent	V D = O V	$T_{VJ} = -40$ °C			400	m/
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$			0,25	١
	gate non-trigger current	VD — 73 VDRM	17/3 = 1.10 G			10	m/
I _{GD}	latching current	t _p = 30 μs	T _{VJ} = 25°C			200	m/
I _L	latering current	r				200	1117-
	holding ourrent	$I_{G} = 1 \text{ A}; \text{ di}_{G}/\text{dt} = 1 \text{ A}/\mu$ $V_{D} = 6 \text{ V} R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$			150	m A
I _H	holding current					150	m <i>A</i>
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$			2	με
		$I_G = 1 \text{ A}; \text{ di}_G/\text{dt} = 1 \text{ A}/\mu \text{s}$					1
t _q	turn-off time	$V_R = 100 \text{ V}; I_T = 300 \text{ A}; V = 300 \text{ A}; $			350		με
	$di/dt = 10 \text{ A/}\mu\text{s} \text{ dv/dt} = 50 \text{ V/}\mu\text{s} t_p = 200 \mu\text{s}$						1



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Package Y1				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				600	Α
T _{vJ}	virtual junction temperature			-40		140	°C
Top	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					650		g
M _D	mounting torque			4,5		7	Nm
M _T	terminal torque			11		13	Nm
d _{Spp/App}	creenage distance on surface	l etriking dietance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$	creepage distance on surface striking distance through a		terminal to backside	25,0			mm
V _{ISOL}	isolation voltage	t = 1 second		3600			V
	t = 1 minute	50/60 Hz, RMS; IsoL ≤ 1 mA 3000			V		



Part description

M = Module

M = Module
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
650 = Current Rating [A]

MT = 1~ Triac

1800 = Reverse Voltage [V]

N = Three Quadrants operation: QI - QIII KD = Y1-2-CU

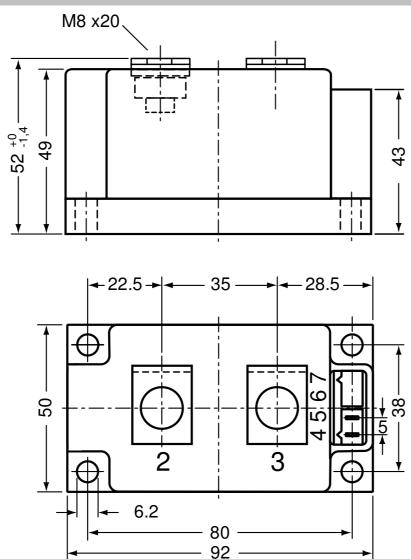
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA650MT1800NKD	MCMA650MT1800NKD	Box	3	518710

Similar Part	Package	Voltage class
MCMA650MT1400NKD	Y1-2-CU	1400

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 140 ^{\circ}\text{C}$
$I \rightarrow V_0$)— <u>R</u> o	Thyristor		
V _{0 max}	threshold voltage	0,81		V
$R_{0\;max}$	slope resistance *	0,5		$m\Omega$

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Outlines Y1



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5) Type ZY 180R (R = Right for pin pair 6/7) UL 758, style 3751

